A new comparison between solid-state thermionics and thermoelectrics

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Abstract

It is shown that the equations for electrical current in solid-state thermionic and thermoelectric devices converge for devices with a width equal to the mean free path of electrons, yielding a common expression for intensive electronic efficiency in the two types of devices. This result is used to demonstrate that the materials parameters for thermionic and thermoelectric refrigerators are equal, rather than differing by a multiplicative factor as previously thought.

Solid-state thermionic devices may be distinguished from thermoelectric devices according to whether electron transport is ballistic or diffusive [1]. There is, however, little to distinguish the underlying thermodynamics of the two types of devices, with both achieving reversibility under the same conditions [2, 3], and both being governed by the same 'materials parameter' [4, 5, 6]. In previous work, a proportionality factor of $F_0/F_{1/2}\sqrt{\pi}/2$ where F_n is a Fermi integral, was found between the two materials parameters [5]. Here we show that the equations for diffusive and ballistic transport converge for devices with a width equal to the mean-free-path of electrons. This results in a common equation for intensive electronic efficiency for both thermionic and thermoelectric devices, and a proportionality factor between their material parameters equal to unity. We explain the discrepancy between this and previous work by pointing out an inconsistency in the energy dependency of the relaxation time in two equations for conductivity used in [5].

Current in both thermionic and thermoelectric devices can be expressed as

$$J = \iiint j(k)\,dk \tag{1}$$

where $j(k)\ k$ is the net 'energy-resolved' current of electrons flowing in the direction opposite to the temperature gradient with momentum in the range k around k. In thermionic devices with a width less than the mean-free-path, most electrons travel ballistically from one reservoir to another. In this case the energy resolved current density is given by (with dependence upon k implicit)

$$j^b(k)\ k = q D_r\ v_x\ \ f_0\ k \tag{2}$$

where $D_r(k)$ is the density of states (DOS) in the reservoirs, (k) is the probability that electrons are transmitted between the reservoirs, $v_x(k)$ is the velocity in the direction of transport, and $f_0 = [f_0(k; _C; T_C)\ \ f_0(k; _H; T_H)]$ is the difference in the Fermi occupation of states in the cold/hot reservoirs where

$$f_0(k; ; T) = \left[1 + \exp\left(\frac{E(k)}{kT}\right)\right]^{1}. \tag{3}$$

and where $_{C/H}$ is the electrochemical potential and $T_{C/H}$ the temperature of electrons at the hot/cold ends of the device.

Here we follow previous work [5], and assume the transmission probability depends upon the total momentum of electrons rather than momentum in the direction of transport only,

allowing a direct comparison with thermoelectrics in which the energy of mobile electrons is also restricted in all three dimensions (this assumption is made implicitly in [5], between Eq. 1.1 and Eq. 1.3). The theoretical differences between thermionic devices in which the transmission probability is a function of k and k_x are explored in detail in other papers [7, 8, 9].

In thermoelectric devices the energy-resolved diffusive electron current density may be obtained from the Boltzmann transport equation under the relaxation time approximation, and can be written as [10]

$$j^d(k)\ k = qD_1\ v_x^2 \frac{df_0}{dx}\ k \tag{4}$$

where $D_1(k)$ is the local DOS, $(k) = {}_0E\ (k)^r$ is the relaxation time in the direction of transport.

In solid-state power generators and refrigerators with a width close to the electronic mean-free-path it is expected that equations 2 and 4 should yield the same results. To show this, we take the energy dependence of the relaxation time to be $r = 1/2$, which corresponds to scattering that is dominated by acoustic phonons, and results in a mean-free-path in the direction of transport, $v_x(k)\ (k)$, which is independent of energy [5]. We also note that $df_0(x)/dx\ [f_0(x) - f_0(x + x)]/x$ when x is small, so that, for a piece of thermoelectric material $L = $ in length, $df_0(x)/dx\ f_0/$, and equation 4 becomes

$$j^d(k)\ k = qD_1 v_x\ f_0\ k: \tag{5}$$

It can be seen that equations 2 and 5 have the same form, where the product of the DOS in the reservoirs and the transmission probability in Eq. 2 plays the same role in determining the energy spectrum of electrons which carry current as the local DOS does in Eq. 5. This simple result provides an additional underpinning for Ulrich, Barnes and Vining's observation in [5] that thermionic and thermoelectric devices refrigerate (or generate power) via the same underlying physical mechanism. To show that there is no sharp transition in the behavior of a solid-state power generator or refrigerator as its width changes from $L < $ to $L > $, one can use the fact that the probability that an electron can travel a distance L without suffering a collision is [11]

$$P = \exp(-L/) \tag{6}$$

to obtain an equation for energy-resolved current density useful in solid-state power generators and refrigerators of length L as

$$j(k)\ k = qv_x\ f_0\ \ \frac{}{L}D_l[1\ \ P\ ]+ D_r\ P\ \ \ k. \tag{7}$$

which can easily be generalized to the case where ! (k).

Equality between equations 2 and 5 results in a common expression for the electronic e ciency [12] (in thermionic devices) and intensive e ciency [13, 14] (across a small section of thermoelectric material) of

$$^{b}_{PG} = VJ=Q_H \tag{8}$$

for a solid-state power generator and

$$^{b}_{R} = Q_C=VJ \tag{9}$$

for a solid-state refrigerator, where the heat ux density in the cold/hot reservoir of a thermionic device, or at the cold/hot ends of the small section of thermoelectric is given by

$$Q_{C=H} = \int\int\int E(k)\ \ _{C=H}\ \frac{j(k)}{q}dk \tag{10}$$

where the -/+ refers to the cold/hot case, and it is assumed that the temperature gradient, electric eld (" = V=L), and current have no components in the y and z dimensions. It is important to point out that the Eq. 10 considers only heat carried by electrons. If phonon mediated heat leaks are also considered, then two extra terms should be added to Eq. 10, the rst being T_l=L, where _l is the thermal conductivity of the lattice, while the second accounts for 'Joule' heat released by electrons which di use between the hot and cold reservoirs, part of which is then carried by phonons to each end of the device. Shakouri et al. [15] have shown that in the limit that L then heat exactly half of this heat, VJ, is deposited in the hot and cold reservoirs, while if L this heat is entirely deposited in the reservoir recieving the net current of electrons.

Finally, it can be shown that the above results yield the same expression for the materials parameter in thermionic and thermoelectric refrigerators. Assuming a dispersion relation of E = ~²k²=2m , and three-dimensional reservoirs so that D = 1=(2)³, Eq. 2 may be used to obtain the same thermionic materials parameter as found in [5], expressed in terms of the mean-free-path as

$$_{TI} = \frac{}{_l}\frac{4\ m\ \ k}{h^3}\ (kT_C)^2 \tag{11}$$

where $_l$ is the thermal conductivity of the lattice. The thermoelectric materials parameter may be obtained from [5]

$$= \frac{T}{_l}\frac{k^2}{q^2}F_0( )^{-1} \tag{12}$$

where is the electrical conductivity and F_n is a Fermi integral, given by

$$F_n( ) = \frac{1}{(n+1)}\int_0^{Z_1} \frac{^n}{\exp( ) + 1}d \tag{13}$$

where the reduced Fermi energy is $= (E^0)=kT_C$ and E^0 is the height of the barrier in thermionic devices (so that $= 0$ for $E < E^0$, $= 1$ for $E > E^0$) or the conduction band edge in a piece of thermoelectric. Using the same dispersion relation and density of states as for thermionic devices we can write an equation for conductivity in thermoelectric materials as

$$\frac{qJ^d}{d=dx} = \frac{4 m q^2}{h^3}\int^Z E\frac{df_0(E)}{dE}dE \tag{14}$$

$$= \frac{4 m k}{h^3}q^2TF_0( ) \tag{15}$$

where we have used the fact that $df_0=dx = (d=dx)(df_0=d)$ for $dT=dx = 0$, that $df_0=d = df_0=dE$, and have integrated by parts to obtain the final line. It can be seen by substitution that this yields $= _{TI}$ if $T = T_C$.

In [5] the thermionic and thermoelectric materials parameters were expressed in terms of the mobility of electrons. In order to do this for the thermoelectric materials parameter, two different expressions for conductivity were equated:

$$= q^2\int^Z v_x^2 D_1\frac{df_0}{dE}dE \tag{16}$$

where $= _0E^{1=2}$, and

$$= nq = q\int^Z D_1f_0dE \tag{17}$$

$$= \frac{q^2}{m}\int^Z D_1E\frac{df_0}{dE}. \tag{18}$$

Given that v_x^2 / E and $q=m$, it can be seen that the two equations do not give the same result for conductivity as the relaxation time is assumed to be proportional to $E^{1=2}$ in the first and independent of energy in the second, and this difficulty results in the factor of $F_0=F_{1=2}$ identified in [5].

In summary, it has been shown that solid-state thermionic and thermoelectric devices with a width close to the mean-free-path of electrons share a common equation for electrical current density and electronic efficiency, and that their 'material parameters' for refrigeration are equal.

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